FIG. 1

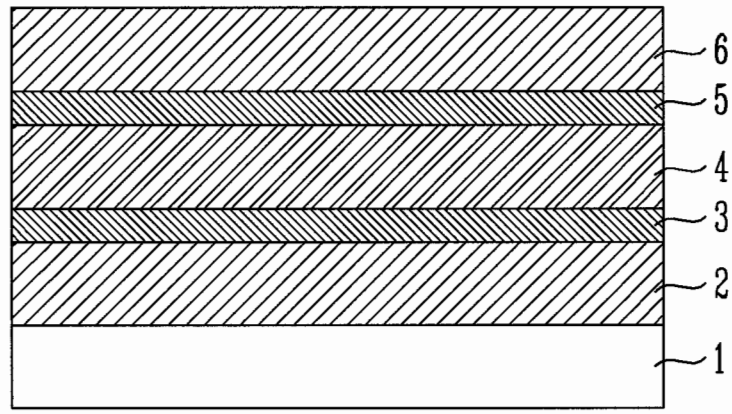
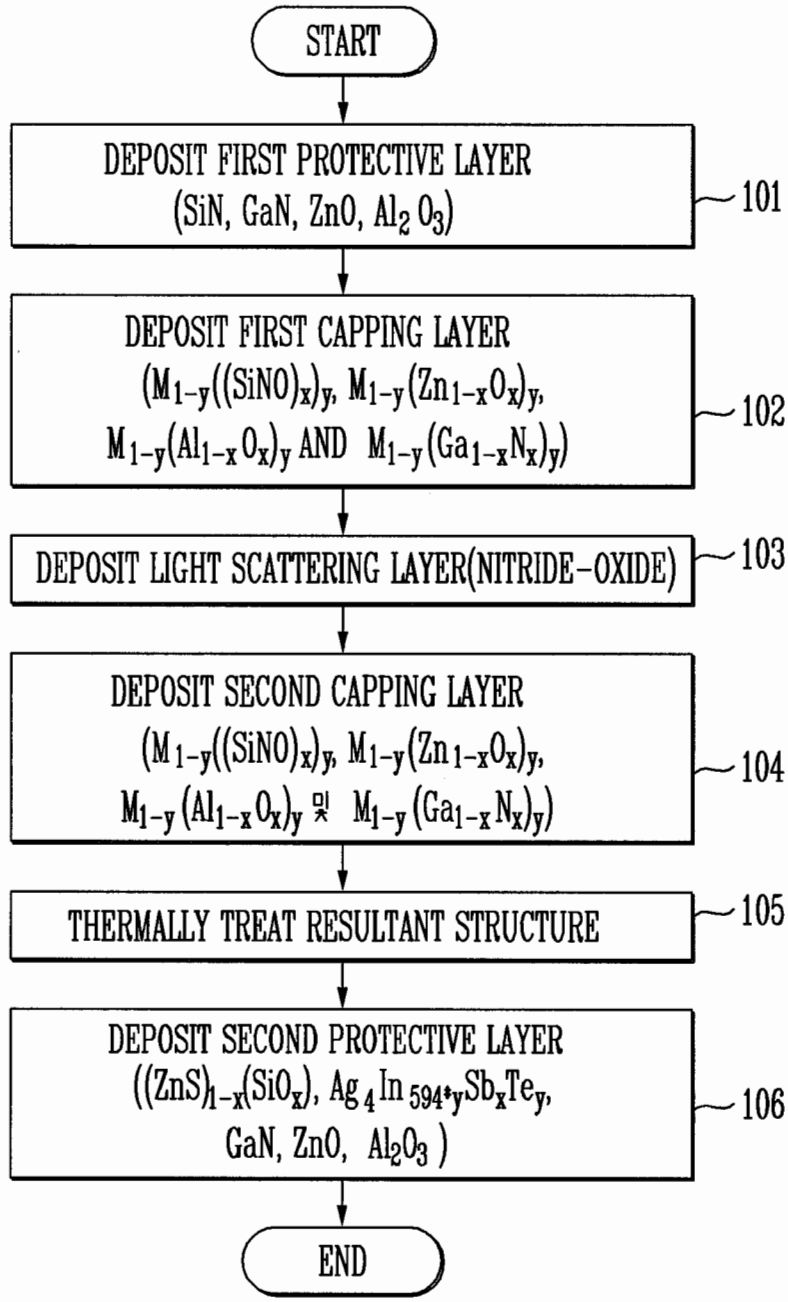


FIG. 2


START
DEPOSIT FIRST PROTECTIVE LAYER
(SiN, GaN, ZnO, Al_2O_3)
101
DEPOSIT FIRST CAPPING LAYER
($M_{1-y}((SiNO)_x)_y$, $M_{1-y}(Zn_{1-x}O_x)_y$,
$M_{1-y}(Al_{1-x}O_x)_y$ AND $M_{1-y}(Ga_{1-x}N_x)_y$)
102
DEPOSIT LIGHT SCATTERING LAYER(NITRIDE-OXIDE)
103
DEPOSIT SECOND CAPPING LAYER
($M_{1-y}((SiNO)_x)_y$, $M_{1-y}(Zn_{1-x}O_x)_y$,
$M_{1-y}(Al_{1-x}O_x)_y$ 및 $M_{1-y}(Ga_{1-x}N_x)_y$)
104
THERMALLY TREAT RESULTANT STRUCTURE
105
DEPOSIT SECOND PROTECTIVE LAYER
($(ZnS)_{1-x}(SiO_x)$, $Ag_4In_{594+y}Sb_xTe_y$,
GaN, ZnO, Al_2O_3)
106
END